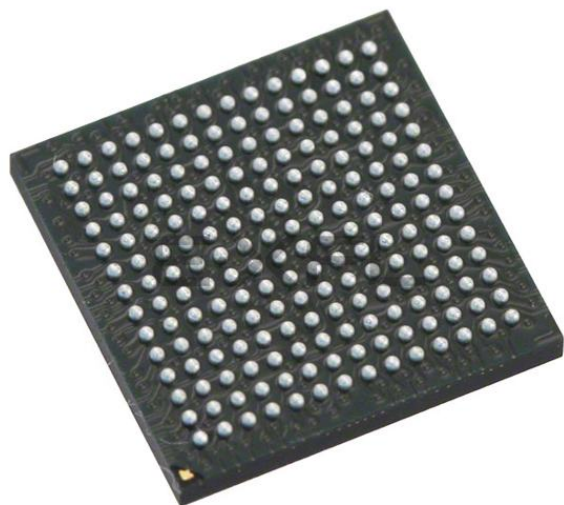




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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	6000
Total RAM Bits	184320
Number of I/O	100
Number of Gates	-
Voltage - Supply	0.95V ~ 1.05V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	196-TFBGA, CSBGA
Supplier Device Package	196-CSPBGA (8x8)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xc7s6-1cpga196i

Table 3: DC Characteristics Over Recommended Operating Conditions

Symbol	Description	Min	Typ ⁽¹⁾	Max	Units
V_{DRINT}	Data retention V_{CCINT} voltage (below which configuration data might be lost).	0.75	–	–	V
V_{DRI}	Data retention V_{CCAUX} voltage (below which configuration data might be lost).	1.5	–	–	V
I_{REF}	V_{REF} leakage current per pin.	–	–	15	μA
I_L	Input or output leakage current per pin (sample-tested).	–	–	15	μA
$C_{IN}^{(2)}$	Die input capacitance at the pad.	–	–	8	pF
I_{RPU}	Pad pull-up (when selected) at $V_{IN} = 0V$, $V_{CCO} = 3.3V$.	90	–	330	μA
	Pad pull-up (when selected) at $V_{IN} = 0V$, $V_{CCO} = 2.5V$.	68	–	250	μA
	Pad pull-up (when selected) at $V_{IN} = 0V$, $V_{CCO} = 1.8V$.	34	–	220	μA
	Pad pull-up (when selected) at $V_{IN} = 0V$, $V_{CCO} = 1.5V$.	23	–	150	μA
	Pad pull-up (when selected) at $V_{IN} = 0V$, $V_{CCO} = 1.2V$.	12	–	120	μA
I_{RPD}	Pad pull-down (when selected) at $V_{IN} = 3.3V$.	68	–	330	μA
I_{CCADC}	Analog supply current, analog circuits in powered up state.	–	–	25	mA
$I_{BATT}^{(3)}$	Battery supply current.	–	–	150	nA
$R_{IN_TERM}^{(4)}$	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ (UNTUNED_SPLIT_40).	28	40	55	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ (UNTUNED_SPLIT_50).	35	50	65	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ (UNTUNED_SPLIT_60).	44	60	83	Ω
n	Temperature diode ideality factor.	–	1.010	–	–
r	Temperature diode series resistance.	–	2	–	Ω

Notes:

1. Typical values are specified at nominal voltage, 25°C.
2. This measurement represents the die capacitance at the pad, not including the package.
3. Maximum value specified for worst case process at 25°C.
4. Termination resistance to a $V_{CCO}/2$ level.

DC Input and Output Levels

Values for V_{IL} and V_{IH} are recommended input voltages. Values for I_{OL} and I_{OH} are guaranteed over the recommended operating conditions at the V_{OL} and V_{OH} test points. Only selected standards are tested. These are chosen to ensure that all standards meet their specifications. The selected standards are tested at a minimum V_{CCO} with the respective V_{OL} and V_{OH} voltage levels shown. Other standards are sample tested.

Table 8: SelectIO DC Input and Output Levels⁽¹⁾⁽²⁾⁽³⁾

I/O Standard	V_{IL}		V_{IH}		V_{OL}	V_{OH}	I_{OL}	I_{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA, Max	mA, Min
HSTL_I	-0.300	$V_{REF} - 0.100$	$V_{REF} + 0.100$	$V_{CCO} + 0.300$	0.400	$V_{CCO} - 0.400$	8.00	-8.00
HSTL_I_18	-0.300	$V_{REF} - 0.100$	$V_{REF} + 0.100$	$V_{CCO} + 0.300$	0.400	$V_{CCO} - 0.400$	8.00	-8.00
HSTL_II	-0.300	$V_{REF} - 0.100$	$V_{REF} + 0.100$	$V_{CCO} + 0.300$	0.400	$V_{CCO} - 0.400$	16.00	-16.00
HSTL_II_18	-0.300	$V_{REF} - 0.100$	$V_{REF} + 0.100$	$V_{CCO} + 0.300$	0.400	$V_{CCO} - 0.400$	16.00	-16.00
HSUL_12	-0.300	$V_{REF} - 0.130$	$V_{REF} + 0.130$	$V_{CCO} + 0.300$	20% V_{CCO}	80% V_{CCO}	0.10	-0.10
LVC MOS12	-0.300	35% V_{CCO}	65% V_{CCO}	$V_{CCO} + 0.300$	0.400	$V_{CCO} - 0.400$	Note 4	Note 4
LVC MOS15	-0.300	35% V_{CCO}	65% V_{CCO}	$V_{CCO} + 0.300$	25% V_{CCO}	75% V_{CCO}	Note 5	Note 5
LVC MOS18	-0.300	35% V_{CCO}	65% V_{CCO}	$V_{CCO} + 0.300$	0.450	$V_{CCO} - 0.450$	Note 6	Note 6
LVC MOS25	-0.300	0.7	1.700	$V_{CCO} + 0.300$	0.400	$V_{CCO} - 0.400$	Note 5	Note 5
LVC MOS33	-0.300	0.8	2.000	3.450	0.400	$V_{CCO} - 0.400$	Note 5	Note 5
LV TTL	-0.300	0.8	2.000	3.450	0.400	2.400	Note 6	Note 6
MOBILE_DDR	-0.300	20% V_{CCO}	80% V_{CCO}	$V_{CCO} + 0.300$	10% V_{CCO}	90% V_{CCO}	0.10	-0.10
PCI33_3	-0.400	30% V_{CCO}	50% V_{CCO}	$V_{CCO} + 0.500$	10% V_{CCO}	90% V_{CCO}	1.50	-0.50
SSTL135	-0.300	$V_{REF} - 0.090$	$V_{REF} + 0.090$	$V_{CCO} + 0.300$	$V_{CCO}/2 - 0.150$	$V_{CCO}/2 + 0.150$	13.00	-13.00
SSTL135_R	-0.300	$V_{REF} - 0.090$	$V_{REF} + 0.090$	$V_{CCO} + 0.300$	$V_{CCO}/2 - 0.150$	$V_{CCO}/2 + 0.150$	8.90	-8.90
SSTL15	-0.300	$V_{REF} - 0.100$	$V_{REF} + 0.100$	$V_{CCO} + 0.300$	$V_{CCO}/2 - 0.175$	$V_{CCO}/2 + 0.175$	13.00	-13.00
SSTL15_R	-0.300	$V_{REF} - 0.100$	$V_{REF} + 0.100$	$V_{CCO} + 0.300$	$V_{CCO}/2 - 0.175$	$V_{CCO}/2 + 0.175$	8.90	-8.90
SSTL18_I	-0.300	$V_{REF} - 0.125$	$V_{REF} + 0.125$	$V_{CCO} + 0.300$	$V_{CCO}/2 - 0.470$	$V_{CCO}/2 + 0.470$	8.00	-8.00
SSTL18_II	-0.300	$V_{REF} - 0.125$	$V_{REF} + 0.125$	$V_{CCO} + 0.300$	$V_{CCO}/2 - 0.600$	$V_{CCO}/2 + 0.600$	13.40	-13.40

Notes:

1. Tested according to relevant specifications.
2. 3.3V and 2.5V standards are only supported in HR I/O banks.
3. For detailed interface specific DC voltage levels, see the *7 Series FPGAs SelectIO Resources User Guide* (UG471) [Ref 3].
4. Supported drive strengths of 4, 8, or 12 mA in HR I/O banks.
5. Supported drive strengths of 4, 8, 12, or 16 mA in HR I/O banks.
6. Supported drive strengths of 4, 8, 12, 16, or 24 mA in HR I/O banks.

Table 9: Differential SelectIO DC Input and Output Levels

I/O Standard	$V_{ICM}^{(1)}$			$V_{ID}^{(2)}$			$V_{OCM}^{(3)}$			$V_{OD}^{(4)}$		
	V, Min	V, Typ	V, Max	V, Min	V, Typ	V, Max	V, Min	V, Typ	V, Max	V, Min	V, Typ	V, Max
BLVDS_25	0.300	1.200	1.425	0.100	—	—	—	1.250	—	Note 5		
MINI_LVDS_25	0.300	1.200	V_{CCAUX}	0.200	0.400	0.600	1.000	1.200	1.400	0.300	0.450	0.600
PPDS_25	0.200	0.900	V_{CCAUX}	0.100	0.250	0.400	0.500	0.950	1.400	0.100	0.250	0.400
RSDS_25	0.300	0.900	1.500	0.100	0.350	0.600	1.000	1.200	1.400	0.100	0.350	0.600
TMDS_33	2.700	2.965	3.230	0.150	0.675	1.200	$V_{CCO} - 0.405$	$V_{CCO} - 0.300$	$V_{CCO} - 0.190$	0.400	0.600	0.800

Notes:

- V_{ICM} is the input common mode voltage.
- V_{ID} is the input differential voltage ($Q - \overline{Q}$).
- V_{OCM} is the output common mode voltage.
- V_{OD} is the output differential voltage ($Q - \overline{Q}$).
- V_{OD} for BLVDS will vary significantly depending on topology and loading.

Table 10: Complementary Differential SelectIO DC Input and Output Levels

I/O Standard	$V_{ICM}^{(1)}$			$V_{ID}^{(2)}$		$V_{OL}^{(3)}$	$V_{OH}^{(4)}$	I_{OL}	I_{OH}
	V, Min	V, Typ	V, Max	V, Min	V, Max	V, Max	V, Min	mA, Max	mA, Min
DIFF_HSTL_I	0.300	0.750	1.125	0.100	—	0.400	$V_{CCO} - 0.400$	8.00	–8.00
DIFF_HSTL_I_18	0.300	0.900	1.425	0.100	—	0.400	$V_{CCO} - 0.400$	8.00	–8.00
DIFF_HSTL_II	0.300	0.750	1.125	0.100	—	0.400	$V_{CCO} - 0.400$	16.00	–16.00
DIFF_HSTL_II_18	0.300	0.900	1.425	0.100	—	0.400	$V_{CCO} - 0.400$	16.00	–16.00
DIFF_HSUL_12	0.300	0.600	0.850	0.100	—	20% V_{CCO}	80% V_{CCO}	0.100	–0.100
DIFF_MOBILE_DDR	0.300	0.900	1.425	0.100	—	10% V_{CCO}	90% V_{CCO}	0.100	–0.100
DIFF_SSTL135	0.300	0.675	1.000	0.100	—	$(V_{CCO}/2) - 0.150$	$(V_{CCO}/2) + 0.150$	13.0	–13.0
DIFF_SSTL135_R	0.300	0.675	1.000	0.100	—	$(V_{CCO}/2) - 0.150$	$(V_{CCO}/2) + 0.150$	8.9	–8.9
DIFF_SSTL15	0.300	0.750	1.125	0.100	—	$(V_{CCO}/2) - 0.175$	$(V_{CCO}/2) + 0.175$	13.0	–13.0
DIFF_SSTL15_R	0.300	0.750	1.125	0.100	—	$(V_{CCO}/2) - 0.175$	$(V_{CCO}/2) + 0.175$	8.9	–8.9
DIFF_SSTL18_I	0.300	0.900	1.425	0.100	—	$(V_{CCO}/2) - 0.470$	$(V_{CCO}/2) + 0.470$	8.00	–8.00
DIFF_SSTL18_II	0.300	0.900	1.425	0.100	—	$(V_{CCO}/2) - 0.600$	$(V_{CCO}/2) + 0.600$	13.4	–13.4

Notes:

- V_{ICM} is the input common mode voltage.
- V_{ID} is the input differential voltage ($Q - \overline{Q}$).
- V_{OL} is the single-ended low-output voltage.
- V_{OH} is the single-ended high-output voltage.

LVDS DC Specifications (LVDS_25)

Table 11: LVDS_25 DC Specifications⁽¹⁾

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
V_{CCO}	Supply voltage.		2.375	2.500	2.625	V
V_{OH}	Output High voltage for Q and $\overline{Q}$.	$R_T = 100\Omega$ across Q and $\overline{Q}$ signals.	–	–	1.675	V
V_{OL}	Output Low voltage for Q and $\overline{Q}$.	$R_T = 100\Omega$ across Q and $\overline{Q}$ signals.	0.700	–	–	V
V_{ODIFF}	Differential output voltage: (Q – $\overline{Q}$), Q = High ($\overline{Q}$ – Q), $\overline{Q}$ = High	$R_T = 100\Omega$ across Q and $\overline{Q}$ signals.	247	350	600	mV
V_{OCM}	Output common-mode voltage.	$R_T = 100\Omega$ across Q and $\overline{Q}$ signals.	1.000	1.250	1.425	V
V_{IDIFF}	Differential input voltage: (Q – $\overline{Q}$), Q = High ($\overline{Q}$ – Q), $\overline{Q}$ = High		100	350	600	mV
V_{ICM}	Input common-mode voltage.		0.300	1.200	1.500	V

Notes:

1. Differential inputs for LVDS_25 can be placed in banks with V_{CCO} levels that are different from the required level for outputs. Consult the *7 Series FPGAs SelectIO Resources User Guide* (UG471) [Ref 3] for more information.

Table 17: IOB High Range (HR) Switching Characteristics (Cont'd)

I/O Standard	T _{IOPI}			T _{IOOP}			T _{IOTP}			Units
	V _{CCINT} Operating Voltage and Speed Grade									
	1.0V		0.95V	1.0V		0.95V	1.0V		0.95V	
	-2	-1	-1L	-2	-1	-1L	-2	-1	-1L	
LVC MOS15_F8	0.86	0.93	0.93	1.72	1.98	1.98	1.75	1.99	1.99	ns
LVC MOS15_F12	0.86	0.93	0.93	1.47	1.73	1.73	1.50	1.74	1.74	ns
LVC MOS15_F16	0.86	0.93	0.93	1.46	1.71	1.71	1.49	1.73	1.73	ns
LVC MOS12_S4	0.95	1.02	1.02	2.69	2.95	2.95	2.72	2.96	2.96	ns
LVC MOS12_S8	0.95	1.02	1.02	2.21	2.46	2.46	2.24	2.48	2.48	ns
LVC MOS12_S12	0.95	1.02	1.02	1.91	2.17	2.17	1.94	2.18	2.18	ns
LVC MOS12_F4	0.95	1.02	1.02	2.10	2.35	2.35	2.13	2.37	2.37	ns
LVC MOS12_F8	0.95	1.02	1.02	1.66	1.92	1.92	1.69	1.93	1.93	ns
LVC MOS12_F12	0.95	1.02	1.02	1.51	1.76	1.76	1.54	1.77	1.77	ns
SSTL135_S	0.75	0.82	0.82	1.47	1.73	1.73	1.50	1.74	1.74	ns
SSTL15_S	0.68	0.75	0.75	1.43	1.68	1.68	1.46	1.69	1.69	ns
SSTL18_I_S	0.75	0.82	0.82	1.79	2.04	2.04	1.82	2.06	2.06	ns
SSTL18_II_S	0.75	0.82	0.82	1.43	1.68	1.68	1.46	1.70	1.70	ns
DIFF_SSTL135_S	0.76	0.83	0.83	1.47	1.73	1.73	1.50	1.74	1.74	ns
DIFF_SSTL15_S	0.76	0.83	0.83	1.43	1.68	1.68	1.46	1.69	1.69	ns
DIFF_SSTL18_I_S	0.79	0.86	0.86	1.80	2.06	2.06	1.83	2.07	2.07	ns
DIFF_SSTL18_II_S	0.79	0.86	0.86	1.51	1.76	1.76	1.54	1.77	1.77	ns
SSTL135_F	0.75	0.82	0.82	1.24	1.49	1.49	1.27	1.51	1.51	ns
SSTL15_F	0.68	0.75	0.75	1.19	1.45	1.45	1.22	1.46	1.46	ns
SSTL18_I_F	0.75	0.82	0.82	1.24	1.49	1.49	1.27	1.51	1.51	ns
SSTL18_II_F	0.75	0.82	0.82	1.24	1.49	1.49	1.27	1.51	1.51	ns
DIFF_SSTL135_F	0.76	0.83	0.83	1.24	1.49	1.49	1.27	1.51	1.51	ns
DIFF_SSTL15_F	0.76	0.83	0.83	1.19	1.45	1.45	1.22	1.46	1.46	ns
DIFF_SSTL18_I_F	0.79	0.86	0.86	1.35	1.60	1.60	1.38	1.62	1.62	ns
DIFF_SSTL18_II_F	0.79	0.86	0.86	1.33	1.59	1.59	1.36	1.60	1.60	ns

Table 18 specifies the values of T_{IOTPHZ} and $T_{IOIBUFDISABLE}$. T_{IOTPHZ} is described as the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is enabled (i.e., a high impedance state). $T_{IOIBUFDISABLE}$ is described as the IOB delay from IBUFDISABLE to O output. In HR I/O banks, the internal IN_TERM termination turn-off time is always faster than T_{IOTPHZ} when the INTERMDISABLE pin is used.

Table 18: IOB 3-state Output Switching Characteristics

Symbol	Description	V _{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
T _{IOTPHZ}	T input to pad high-impedance.	2.19	2.37	2.37	ns
T _{IOIBUFDISABLE}	IBUF turn-on time from IBUFDISABLE to O output.	2.30	2.60	2.60	ns

Input Serializer/Deserializer Switching Characteristics

Table 23: ISERDES Switching Characteristics

Symbol	Description	V _{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
Setup/Hold for Control Lines					
T _{ISCKK_BITSLIP} / T _{ISCKC_BITSLIP}	BITSLIP pin setup/hold with respect to CLKDIV.	0.02/0.15	0.02/0.17	0.02/0.17	ns
T _{ISCKK_CE} / T _{ISCKC_CE}	CE pin setup/hold with respect to CLK (for CE1).	0.50/−0.01	0.72/−0.01	0.72/−0.01	ns
T _{ISCKK_CE2} / T _{ISCKC_CE2}	CE pin setup/hold with respect to CLKDIV (for CE2).	−0.10/0.36	−0.10/0.40	−0.10/0.40	ns
Setup/Hold for Data Lines					
T _{ISDCK_D} / T _{ISCKD_D}	D pin setup/hold with respect to CLK.	−0.02/0.14	−0.02/0.17	−0.02/0.17	ns
T _{ISDCK_DDLY} / T _{ISCKD_DDLY}	DDLY pin setup/hold with respect to CLK (using IDELAY). ⁽¹⁾	−0.02/0.14	−0.02/0.17	−0.02/0.17	ns
T _{ISDCK_D_DDR} / T _{ISCKD_D_DDR}	D pin setup/hold with respect to CLK at DDR mode.	−0.02/0.14	−0.02/0.17	−0.02/0.17	ns
T _{ISDCK_DDLY_DDR} / T _{ISCKD_DDLY_DDR}	D pin setup/hold with respect to CLK at DDR mode (using IDELAY). ⁽¹⁾	0.14/0.14	0.17/0.17	0.17/0.17	ns
Sequential Delays					
T _{ISCKO_Q}	CLKDIV to out at Q pin.	0.54	0.66	0.66	ns
Propagation Delays					
T _{ISDO_DO}	D input to DO output pin.	0.11	0.13	0.13	ns

Notes:

- Recorded at 0 tap value.

Output Serializer/Deserializer Switching Characteristics

Table 24: OSERDES Switching Characteristics

Symbol	Description	V _{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
Setup/Hold					
T _{OSDCK_D} / T _{OSCKD_D}	D input setup/hold with respect to CLKDIV.	0.45/0.03	0.63/0.03	0.63/0.03	ns
T _{OSDCK_T} / T _{OSCKD_T}	T input setup/hold with respect to CLK.	0.73/−0.13	0.88/−0.13	0.88/−0.13	ns
T _{OSDCK_T2} / T _{OSCKD_T2}	T input setup/hold with respect to CLKDIV.	0.34/−0.13	0.39/−0.13	0.39/−0.13	ns
T _{OSCKCK_OCE} / T _{OSCKC_OCE}	OCE input setup/hold with respect to CLK.	0.34/0.58	0.51/0.58	0.51/0.58	ns
T _{OSCKCK_S}	SR (reset) input setup with respect to CLKDIV.	0.52	0.85	0.85	ns
T _{OSCKCK_TCE} / T _{OSCKC_TCE}	TCE input setup/hold with respect to CLK.	0.34/0.01	0.51/0.01	0.51/0.01	ns
Sequential Delays					
T _{OSCKO_OQ}	Clock to out from CLK to OQ.	0.42	0.48	0.48	ns
T _{OSCKO_TQ}	Clock to out from CLK to TQ.	0.49	0.56	0.56	ns
Combinatorial					
T _{OSDO_TTQ}	T input to TQ out.	0.92	1.11	1.11	ns

Table 26: IO_FIFO Switching Characteristics

Symbol	Description	V _{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
IO_FIFO Clock to Out Delays					
T _{OFFCKO_DO}	RDCLK to Q outputs.	0.60	0.68	0.68	ns
T _{CKO_FLAGS}	Clock to IO_FIFO flags.	0.61	0.77	0.77	ns
Setup/Hold					
T _{CCK_D} /T _{CKC_D}	D inputs to WRCLK.	0.51/0.02	0.58/0.02	0.58/0.02	ns
T _{IFFCCK_WREN} / T _{IFFCKC_WREN}	WREN to WRCLK.	0.47/−0.01	0.53/−0.01	0.53/−0.01	ns
T _{OFFCCK_RDEN} / T _{OFFCKC_RDEN}	RDEN to RDCLK.	0.58/0.02	0.66/0.02	0.66/0.02	ns
Minimum Pulse Width					
T _{PWH_IO_FIFO}	RESET, RDCLK, WRCLK.	2.15	2.15	2.15	ns
T _{PWL_IO_FIFO}	RESET, RDCLK, WRCLK.	2.15	2.15	2.15	ns
Maximum Frequency					
F _{MAX}	RDCLK and WRCLK.	200.00	200.00	200.00	MHz

CLB Distributed RAM Switching Characteristics (SLICEM Only)

Table 28: CLB Distributed RAM Switching Characteristics

Symbol	Description	V _{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
Sequential Delays					
T _{SHCKO}	Clock to A – B outputs.	1.09	1.32	1.32	ns, Max
T _{SHCKO_1}	Clock to AMUX – BMUX outputs.	1.53	1.86	1.86	ns, Max
Setup and Hold Times Before/After Clock CLK					
T _{DS_LRAM} /T _{DH_LRAM}	A – D inputs to CLK.	0.60/0.30	0.72/0.35	0.72/0.35	ns, Min
T _{AS_LRAM} /T _{AH_LRAM}	Address An inputs to clock.	0.30/0.60	0.37/0.70	0.37/0.70	ns, Min
	Address An inputs through MUXs and/or carry logic to clock.	0.77/0.21	0.94/0.26	0.94/0.26	ns, Min
T _{WS_LRAM} /T _{WH_LRAM}	WE input to clock.	0.43/0.12	0.53/0.17	0.53/0.17	ns, Min
T _{CECK_LRAM} /T _{CKCE_LRAM}	CE input to CLK.	0.44/0.11	0.53/0.17	0.53/0.17	ns, Min
Clock CLK					
T _{MPW_LRAM}	Minimum pulse width.	1.13	1.25	1.25	ns, Min
T _{MCP}	Minimum clock period.	2.26	2.50	2.50	ns, Min

Notes:

1. T_{SHCKO} also represents the CLK to XMUX output. Refer to the timing report for the CLK to XMUX path.

CLB Shift Register Switching Characteristics (SLICEM Only)

Table 29: CLB Shift Register Switching Characteristics

Symbol	Description	V _{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
Sequential Delays					
T _{REG}	Clock to A – D outputs.	1.33	1.61	1.61	ns, Max
T _{REG_MUX}	Clock to AMUX – DMUX output.	1.77	2.15	2.15	ns, Max
T _{REG_M31}	Clock to DMUX output via M31 output.	1.23	1.46	1.46	ns, Max
Setup and Hold Times Before/After Clock CLK					
T _{WS_SHFREG} / T _{WH_SHFREG}	WE input.	0.41/0.12	0.51/0.17	0.51/0.17	ns, Min
T _{CECK_SHFREG} / T _{CKCE_SHFREG}	CE input to CLK.	0.42/0.11	0.52/0.17	0.52/0.17	ns, Min
T _{DS_SHFREG} / T _{DH_SHFREG}	A – D inputs to CLK.	0.37/0.37	0.44/0.43	0.44/0.43	ns, Min
Clock CLK					
T _{MPW_SHFREG}	Minimum pulse width.	0.86	0.98	0.98	ns, Min

Table 31: DSP48E1 Switching Characteristics (Cont'd)

Symbol	Description	V _{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
T _{DSPDCK_CEM_MREG} / T _{DSPCKD_CEM_MREG}	CEM input to M register CLK.	0.21/ 0.20	0.27/ 0.23	0.27/ 0.23	ns
T _{DSPDCK_CEP_PREG} / T _{DSPCKD_CEP_PREG}	CEP input to P register CLK.	0.43/ 0.01	0.53/ 0.01	0.53/ 0.01	ns
Setup and Hold Times of the RST Pins					
T _{DSPDCK_{RSTA; RSTB}_{AREG; BREG}}} / T _{DSPCKD_{RSTA; RSTB}_{AREG; BREG}}}	{RSTA, RSTB} input to {A, B} register CLK.	0.46/ 0.13	0.55/ 0.15	0.55/ 0.15	ns
T _{DSPDCK_RSTC_CREG} / T _{DSPCKD_RSTC_CREG}	RSTC input to C register CLK.	0.08/ 0.11	0.09/ 0.12	0.09/ 0.12	ns
T _{DSPDCK_RSTD_DREG} / T _{DSPCKD_RSTD_DREG}	RSTD input to D register CLK	0.50/ 0.08	0.59/ 0.09	0.59/ 0.09	ns
T _{DSPDCK_RSTM_MREG} / T _{DSPCKD_RSTM_MREG}	RSTM input to M register CLK	0.23/ 0.24	0.27/ 0.28	0.27/ 0.28	ns
T _{DSPDCK_RSTP_PREG} / T _{DSPCKD_RSTP_PREG}	RSTP input to P register CLK	0.30/ 0.01	0.35/ 0.01	0.35/ 0.01	ns
Combinatorial Delays from Input Pins to Output Pins					
T _{DSPDO_A_CARRYOUT_MULT}	A input to CARRYOUT output using multiplier.	4.35	5.18	5.18	ns
T _{DSPDO_D_P_MULT}	D input to P output using multiplier.	4.26	5.07	5.07	ns
T _{DSPDO_B_P}	B input to P output not using multiplier.	1.75	2.08	2.08	ns
T _{DSPDO_C_P}	C input to P output.	1.53	1.82	1.82	ns
Combinatorial Delays from Input Pins to Cascading Output Pins					
T _{DSPDO_{A; B}_{ACOUT; BCOUT}}}	{A, B} input to {ACOUT, BCOUT} output.	0.63	0.74	0.74	ns
T _{DSPDO_{A, B}_CARRYCASCOUT_MULT}}	{A, B} input to CARRYCASCOUT output using multiplier.	4.65	5.54	5.54	ns
T _{DSPDO_D_CARRYCASCOUT_MULT}	D input to CARRYCASCOUT output using multiplier.	4.54	5.40	5.40	ns
T _{DSPDO_{A, B}_CARRYCASCOUT}	{A, B} input to CARRYCASCOUT output not using multiplier.	2.03	2.41	2.41	ns
T _{DSPDO_C_CARRYCASCOUT}	C input to CARRYCASCOUT output.	1.81	2.15	2.15	ns
Combinatorial Delays from Cascading Input Pins to All Output Pins					
T _{DSPDO_ACIN_P_MULT}	ACIN input to P output using multiplier.	4.19	5.00	5.00	ns
T _{DSPDO_ACIN_P}	ACIN input to P output not using multiplier.	1.57	1.88	1.88	ns
T _{DSPDO_ACIN_ACOUT}	ACIN input to ACOUT output.	0.44	0.53	0.53	ns
T _{DSPDO_ACIN_CARRYCASCOUT_MULT}	ACIN input to CARRYCASCOUT output using multiplier.	4.47	5.33	5.33	ns
T _{DSPDO_ACIN_CARRYCASCOUT}	ACIN input to CARRYCASCOUT output not using multiplier.	1.85	2.21	2.21	ns
T _{DSPDO_PCIN_P}	PCIN input to P output.	1.28	1.52	1.52	ns

Table 31: DSP48E1 Switching Characteristics (Cont'd)

Symbol	Description	V _{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
T _{DSPDO_PCIN_CARRYCASCOUT}	PCIN input to CARRYCASCOUT output.	1.56	1.85	1.85	ns
Clock to Outs from Output Register Clock to Output Pins					
T _{DSPCKO_P_PREG}	CLK PREG to P output.	0.37	0.44	0.44	ns
T _{DSPCKO_CARRYCASCOUT_PREG}	CLK PREG to CARRYCASCOUT output.	0.59	0.69	0.69	ns
Clock to Outs from Pipeline Register Clock to Output Pins					
T _{DSPCKO_P_MREG}	CLK MREG to P output.	1.93	2.31	2.31	ns
T _{DSPCKO_CARRYCASCOUT_MREG}	CLK MREG to CARRYCASCOUT output.	2.21	2.64	2.64	ns
T _{DSPCKO_P_ADREG_MULT}	CLK ADREG to P output using multiplier.	3.10	3.69	3.69	ns
T _{DSPCKO_CARRYCASCOUT_ADREG_MULT}	CLK ADREG to CARRYCASCOUT output using multiplier.	3.38	4.02	4.02	ns
Clock to Outs from Input Register Clock to Output Pins					
T _{DSPCKO_P_AREG_MULT}	CLK AREG to P output using multiplier.	4.51	5.37	5.37	ns
T _{DSPCKO_P_BREG}	CLK BREG to P output not using multiplier.	1.87	2.22	2.22	ns
T _{DSPCKO_P_CREG}	CLK CREG to P output not using multiplier.	1.93	2.30	2.30	ns
T _{DSPCKO_P_DREG_MULT}	CLK DREG to P output using multiplier.	4.48	5.32	5.32	ns
Clock to Outs from Input Register Clock to Cascading Output Pins					
T _{DSPCKO_{ACOUT; BCOUT}_{AREG; BREG}}	CLK (ACOUT, BCOUT) to {A,B} register output.	0.73	0.87	0.87	ns
T _{DSPCKO_CARRYCASCOUT_{AREG; BREG}_MULT}	CLK (AREG, BREG) to CARRYCASCOUT output using multiplier.	4.79	5.70	5.70	ns
T _{DSPCKO_CARRYCASCOUT_BREG}	CLK BREG to CARRYCASCOUT output not using multiplier.	2.15	2.55	2.55	ns
T _{DSPCKO_CARRYCASCOUT_DREG_MULT}	CLK DREG to CARRYCASCOUT output using multiplier.	4.76	5.65	5.65	ns
T _{DSPCKO_CARRYCASCOUT_CREG}	CLK CREG to CARRYCASCOUT output.	2.21	2.63	2.63	ns
Maximum Frequency					
F _{MAX}	With all registers used.	550.66	464.25	464.25	MHz
F _{MAX_PATDET}	With pattern detector.	465.77	392.93	392.93	MHz
F _{MAX_MULT_NOMREG}	Two register multiply without MREG.	305.62	257.47	257.47	MHz
F _{MAX_MULT_NOMREG_PATDET}	Two register multiply without MREG with pattern detect.	277.62	233.92	233.92	MHz
F _{MAX_PREADD_MULT_NOADREG}	Without ADREG.	346.26	290.44	290.44	MHz
F _{MAX_PREADD_MULT_NOADREG_PATDET}	Without ADREG with pattern detect.	346.26	290.44	290.44	MHz
F _{MAX_NOPIPELINEREG}	Without pipeline registers (MREG, ADREG).	227.01	190.69	190.69	MHz
F _{MAX_NOPIPELINEREG_PATDET}	Without pipeline registers (MREG, ADREG) with pattern detect.	211.15	177.43	177.43	MHz

Clock Buffers and Networks

Table 32: Global Clock Switching Characteristics (Including BUFGCTRL)

Symbol	Description	V _{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
T _{BCCCK_CE} /T _{BCCCK_CE} ⁽¹⁾	CE pins setup/hold.	0.13/0.40	0.16/0.41	0.16/0.41	ns
T _{BCCCK_S} /T _{BCCCK_S} ⁽¹⁾	S pins setup/hold.	0.13/0.40	0.16/0.41	0.16/0.41	ns
T _{BCKO_O} ⁽²⁾	BUFGCTRL delay from I0/I1 to O.	0.09	0.10	0.10	ns
Maximum Frequency					
F _{MAX_BUFG}	Global clock tree (BUFG).	628.00	464.00	464.00	MHz

Notes:

1. T_{BCCCK_CE} and T_{BCCCK_CE} must be satisfied to assure glitch-free operation of the global clock when switching between clocks. These parameters do not apply to the BUFGMUX primitive that assures glitch-free operation. The other global clock setup and hold times are optional; only needing to be satisfied if device operation requires simulation matches on a cycle-for-cycle basis when switching between clocks.
2. T_{BCKO_O} (BUFG delay from I0 to O) values are the same as T_{BCKO_O} values.

Table 33: Input/Output Clock Switching Characteristics (BUFIO)

Symbol	Description	V _{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
T _{BIOCKO_O}	Clock to out delay from I to O.	1.26	1.54	1.54	ns
Maximum Frequency					
F _{MAX_BUFIO}	I/O clock tree (BUFIO).	680.00	600.00	600.00	MHz

Table 34: Regional Clock Buffer Switching Characteristics (BUFR)

Symbol	Description	V _{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
T _{BRCKO_O}	Clock to out delay from I to O.	0.76	0.99	0.99	ns
T _{BRCKO_O_BYP}	Clock to out delay from I to O with Divide Bypass attribute set.	0.39	0.52	0.52	ns
T _{BRDO_O}	Propagation delay from CLR to O.	0.85	1.09	1.09	ns
Maximum Frequency					
F _{MAX_BUFR} ⁽¹⁾	Regional clock tree (BUFR).	375.00	315.00	315.00	MHz

Notes:

1. The maximum input frequency to the BUFR is the BUFIO F_{MAX} frequency.

Table 40: Clock-Capable Clock Input to Output Delay Without MMCM/PLL (Far Clock Region)⁽¹⁾

Symbol	Description	Device	V _{CCINT} Operating Voltage and Speed Grade			Units
			1.0V		0.95V	
			-2	-1	-1L	
SSTL15 Clock-Capable Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, <i>without</i> MMCM/PLL.						
T _{ICKOFFAR}	Clock-capable clock input and OUTFF at pins/banks farthest from the BUFGs <i>without</i> MMCM/PLL (far clock region). ⁽²⁾	XC7S6	5.55	6.50	6.50	ns
		XC7S15	5.55	6.50	6.50	ns
		XC7S25	5.55	6.44	6.44	ns
		XC7S50	5.71	6.62	6.62	ns
		XC7S75	6.01	7.02	7.02	ns
		XC7S100	6.01	7.02	7.02	ns
		XA7S6	5.55	6.50	N/A	ns
		XA7S15	5.55	6.50	N/A	ns
		XA7S25	5.55	6.44	N/A	ns
		XA7S50	5.71	6.62	N/A	ns
		XA7S75	6.01	7.02	N/A	ns
		XA7S100	6.01	7.02	N/A	ns

Notes:

1. This table lists representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible IOB and CLB flip-flops are clocked by the global clock net.
2. Refer to the *Die Level Bank Numbering Overview* section of the *7 Series FPGA Packaging and Pinout Specification* (UG475) [Ref 4].

Table 41: Clock-Capable Clock Input to Output Delay With MMCM⁽¹⁾

Symbol	Description	Device	V _{CCINT} Operating Voltage and Speed Grade			Units
			1.0V		0.95V	
			-2	-1	-1L	
SSTL15 Clock-Capable Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, <i>with</i> MMCM.						
T _{ICKOFMMCMCC}	Clock-capable clock input and OUTFF <i>with</i> MMCM. ⁽²⁾	XC7S6	1.03	1.03	1.03	ns
		XC7S15	1.03	1.03	1.03	ns
		XC7S25	1.00	1.00	1.00	ns
		XC7S50	1.00	1.00	1.00	ns
		XC7S75	1.00	1.00	1.00	ns
		XC7S100	1.00	1.00	1.00	ns
		XA7S6	1.03	1.03	N/A	ns
		XA7S15	1.03	1.03	N/A	ns
		XA7S25	1.00	1.00	N/A	ns
		XA7S50	1.00	1.00	N/A	ns
		XA7S75	1.00	1.00	N/A	ns
		XA7S100	1.00	1.00	N/A	ns

Notes:

1. This table lists representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible IOB and CLB flip-flops are clocked by the global clock net.
2. MMCM output jitter is already included in the timing calculation.

Table 42: Clock-Capable Clock Input to Output Delay With PLL⁽¹⁾

Symbol	Description	Device	V _{CCINT} Operating Voltage and Speed Grade			Units
			1.0V		0.95V	
			-2	-1	-1L	
SSTL15 Clock-Capable Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, <i>with</i> PLL.						
T _{ICKOFFPLLCC}	Clock-capable clock input and OUTFF <i>with</i> PLL. ⁽²⁾	XC7S6	0.85	0.85	0.85	ns
		XC7S15	0.85	0.85	0.85	ns
		XC7S25	0.83	0.83	0.83	ns
		XC7S50	0.83	0.83	0.83	ns
		XC7S75	0.83	0.83	0.83	ns
		XC7S100	0.83	0.83	0.83	ns
		XA7S6	0.85	0.85	N/A	ns
		XA7S15	0.85	0.85	N/A	ns
		XA7S25	0.83	0.83	N/A	ns
		XA7S50	0.83	0.83	N/A	ns
		XA7S75	0.83	0.83	N/A	ns
		XA7S100	0.83	0.83	N/A	ns

Notes:

1. This table lists representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible IOB and CLB flip-flops are clocked by the global clock net.
2. PLL output jitter is already included in the timing calculation.

Table 43: Pin-to-Pin, Clock-to-Out using BUFIO

Symbol	Description	V _{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
SSTL15 Clock-Capable Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, with BUFIO.					
T _{ICKOFCS}	Clock to out of I/O clock.	5.61	6.64	6.64	ns

Device Pin-to-Pin Input Parameter Guidelines

All devices are 100% functionally tested. Values are expressed in nanoseconds unless otherwise noted.

Table 44: Global Clock Input Setup and Hold Without MMCM/PLL with ZHOLD_DELAY on HR I/O Banks

Symbol	Description	Device	V _{CCINT} Operating Voltage and Speed Grade			Units
			1.0V		0.95V	
			-2	-1	-1L	
Input Setup and Hold Time Relative to Global Clock Input Signal for SSTL15 Standard. ⁽¹⁾						
T _{PSFD} / T _{PHFD}	Full delay (legacy delay or default delay) global clock input and IFF ⁽²⁾ without MMCM/PLL with ZHOLD_DELAY on HR I/O banks.	XC7S6	2.76/−0.40	3.17/−0.40	3.17/−0.40	ns
		XC7S15	2.76/−0.40	3.17/−0.40	3.17/−0.40	ns
		XC7S25	2.67/−0.37	3.12/−0.37	3.12/−0.37	ns
		XC7S50	2.66/−0.28	3.11/−0.28	3.11/−0.28	ns
		XC7S75	2.91/−0.33	3.36/−0.33	3.36/−0.33	ns
		XC7S100	2.91/−0.33	3.36/−0.33	3.36/−0.33	ns
		XA7S6	2.76/−0.40	3.17/−0.40	N/A	ns
		XA7S15	2.76/−0.40	3.17/−0.40	N/A	ns
		XA7S25	2.67/−0.37	3.12/−0.37	N/A	ns
		XA7S50	2.66/−0.28	3.11/−0.28	N/A	ns
		XA7S75	2.91/−0.33	3.36/−0.33	N/A	ns
		XA7S100	2.91/−0.33	3.36/−0.33	N/A	ns

Notes:

- Setup and hold times are measured over worst case conditions (process, voltage, temperature). Setup time is measured relative to the global clock input signal using the slowest process, highest temperature, and lowest voltage. Hold time is measured relative to the global clock input signal using the fastest process, lowest temperature, and highest voltage.
- IFF = Input flip-flop or latch.

Table 48: Sample Window

Symbol	Description	V _{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
T _{SAMP}	Sampling error at receiver pins. ⁽¹⁾	0.64	0.70	0.70	ns
T _{SAMP_BUFIO}	Sampling error at receiver pins using BUFIO. ⁽²⁾	0.40	0.46	0.46	ns

Notes:

1. This parameter indicates the total sampling error of the Spartan-7 FPGAs DDR input registers, measured across voltage, temperature, and process. The characterization methodology uses the MMCM to capture the DDR input registers' edges of operation. These measurements include:
 - CLK0 MMCM jitter
 - MMCM accuracy (phase offset)
 - MMCM phase shift resolution
These measurements do not include package or clock tree skew.
2. This parameter indicates the total sampling error of the Spartan-7 FPGAs DDR input registers, measured across voltage, temperature, and process. The characterization methodology uses the BUFIO clock network and IDELAY to capture the DDR input registers' edges of operation. These measurements do not include package or clock tree skew.

XADC Specifications

The 7 Series FPGAs Overview (DS180) [Ref 1] and XA Spartan-7 Automotive FPGA Data Sheet: Overview (DS171) [Ref 2] list the devices that contain a 7 series XADC dual 12-Bit 1 MSPS analog-to-digital converter.

Table 50: XADC Specifications

Parameter	Symbol	Comments/Conditions	Min	Typ	Max	Units
$V_{CCADC} = 1.8V \pm 5\%$, $V_{REFP} = 1.25V$, $V_{REFN} = 0V$, $ADCCLK = 26\text{ MHz}$, $-55^{\circ}\text{C} \leq T_j \leq 125^{\circ}\text{C}$. Typical values at $T_j = +40^{\circ}\text{C}$.						
ADC Accuracy⁽¹⁾						
Resolution			12	–	–	Bits
Integral nonlinearity ⁽²⁾	INL	$-40^{\circ}\text{C} \leq T_j \leq 100^{\circ}\text{C}$	–	–	± 2	LSBs
		$-55^{\circ}\text{C} \leq T_j < -40^{\circ}\text{C}$; $100^{\circ}\text{C} < T_j \leq 125^{\circ}\text{C}$	–	–	± 3	LSBs
Differential nonlinearity	DNL	No missing codes, guaranteed monotonic.	–	–	± 1	LSBs
Offset error	Unipolar	$-40^{\circ}\text{C} \leq T_j \leq 100^{\circ}\text{C}$	–	–	± 8	LSBs
		$-55^{\circ}\text{C} \leq T_j < -40^{\circ}\text{C}$; $100^{\circ}\text{C} < T_j \leq 125^{\circ}\text{C}$	–	–	± 12	LSBs
	Bipolar	$-55^{\circ}\text{C} \leq T_j \leq 125^{\circ}\text{C}$	–	–	± 4	LSBs
Gain error			–	–	± 0.5	%
Offset matching			–	–	4	LSBs
Gain matching			–	–	0.3	%
Sample rate			–	–	1	MS/s
Signal to noise ratio ⁽²⁾	SNR	$F_{\text{SAMPLE}} = 500\text{ KS/s}$, $F_{\text{IN}} = 20\text{ kHz}$	60	–	–	dB
RMS code noise		External 1.25V reference.	–	–	2	LSBs
		On-chip reference.	–	3	–	LSBs
Total harmonic distortion ⁽²⁾	THD	$F_{\text{SAMPLE}} = 500\text{ KS/s}$, $F_{\text{IN}} = 20\text{ kHz}$	70	–	–	dB
Analog Inputs⁽³⁾						
ADC input ranges		Unipolar operation.	0	–	1	V
		Bipolar operation.	–0.5	–	+0.5	V
		Unipolar common mode range (FS input).	0	–	+0.5	V
		Bipolar common mode range (FS input).	+0.5	–	+0.6	V
Maximum external channel input ranges		Adjacent analog channels set within these ranges should not corrupt measurements on adjacent channels.	–0.1	–	V_{CCADC}	V
Full-resolution bandwidth	FRBW	Auxiliary channel full resolution bandwidth.	250	–	–	kHz
On-chip Sensors						
Temperature sensor error		$-40^{\circ}\text{C} \leq T_j \leq 100^{\circ}\text{C}$	–	–	± 4	$^{\circ}\text{C}$
		$-55^{\circ}\text{C} \leq T_j < -40^{\circ}\text{C}$; $100^{\circ}\text{C} < T_j \leq 125^{\circ}\text{C}$	–	–	± 6	$^{\circ}\text{C}$
Supply sensor error		$-40^{\circ}\text{C} \leq T_j \leq 100^{\circ}\text{C}$	–	–	± 1	%
		$-55^{\circ}\text{C} \leq T_j < -40^{\circ}\text{C}$; $100^{\circ}\text{C} < T_j \leq 125^{\circ}\text{C}$	–	–	± 2	%

Table 50: XADC Specifications (Cont'd)

Parameter	Symbol	Comments/Conditions	Min	Typ	Max	Units
Conversion Rate⁽⁴⁾						
Conversion time: continuous	t_{CONV}	Number of ADCCLK cycles.	26	–	32	Cycles
Conversion time: event	t_{CONV}	Number of CLK cycles.	–	–	21	Cycles
DRP clock frequency	DCLK	DRP clock frequency.	8	–	250	MHz
ADC clock frequency	ADCCLK	Derived from DCLK.	1	–	26	MHz
DCLK duty cycle			40	–	60	%
XADC Reference⁽⁵⁾						
External reference	V_{REFP}	Externally supplied reference voltage.	1.20	1.25	1.30	V
On-chip reference		Ground V_{REFP} pin to AGND, $-40^{\circ}\text{C} \leq T_j \leq 100^{\circ}\text{C}$	1.2375	1.25	1.2625	V
		Ground V_{REFP} pin to AGND, $-55^{\circ}\text{C} \leq T_j < -40^{\circ}\text{C}; 100^{\circ}\text{C} < T_j \leq 125^{\circ}\text{C}$	1.225	1.25	1.275	V

Notes:

- Offset and gain errors are removed by enabling the XADC automatic gain calibration feature. The values are specified for when this feature is enabled.
- Only specified for bitstream option XADCEnhancedLinearity = ON.
- For a detailed description, see the ADC chapter in the *7 Series FPGAs and Zynq-7000 AP SoC XADC Dual 12-Bit 1 MSPS Analog-to-Digital Converter User Guide* (UG480) [Ref 9].
- For a detailed description, see the *Timing* chapter in the *7 Series FPGAs and Zynq-7000 AP SoC XADC Dual 12-Bit 1 MSPS Analog-to-Digital Converter User Guide* (UG480) [Ref 9].
- Any variation in the reference voltage from the nominal $V_{\text{REFP}} = 1.25\text{V}$ and $V_{\text{REFN}} = 0\text{V}$ will result in a deviation from the ideal transfer function. This also impacts the accuracy of the internal sensor measurements (i.e., temperature and power supply). However, for external ratiometric type applications allowing reference to vary by $\pm 4\%$ is permitted.